

Valery Yu Davydov

List of Publications by Year in descending order

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192
papers

4,148
citations

201385

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193
docs citations

193
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4258
citing authors

#	ARTICLE	IF	CITATIONS
1	Croconic Acid Doped Triglycine Sulfate: Crystal Structure, UV-Vis, FTIR, Raman, Photoluminescence Spectroscopy, and Dielectric Properties. <i>Crystals</i> , 2022, 12, 679.	1.0	3
2	Phonons in Short-Period GaN/AlN Superlattices: Group-Theoretical Analysis, Ab initio Calculations, and Raman Spectra. <i>Nanomaterials</i> , 2021, 11, 286.	1.9	14
3	A Computational and Spectroscopic Study of the Electronic Structure of V2O5-Based Cathode Materials. <i>Journal of Physical Chemistry C</i> , 2021, 125, 5848-5858.	1.5	7
4	Creation of Negatively Charged Boron Vacancies in Hexagonal Boron Nitride Crystal by Electron Irradiation and Mechanism of Inhomogeneous Broadening of Boron Vacancy-Related Spin Resonance Lines. <i>Nanomaterials</i> , 2021, 11, 1373.	1.9	25
5	Modification of the Electronic Structure of Quasi-Free-Standing Graphene by the Adsorption and Intercalation of Mn Atoms. <i>Journal of Experimental and Theoretical Physics</i> , 2021, 132, 906-916.	0.2	3
6	Monolayer- and Thick GaN/AlN Multilayer Heterostructures for Deep-Ultraviolet Optoelectronics. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2100242.	1.2	14
7	Effect of surface morphology on macroscale and microscale optical properties of layered InSe grown by molecular beam epitaxy. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2021, 38, 2579.	0.9	1
8	Photoluminescence Kinetics of Dark and Bright Excitons in Atomically Thin MoS ₂ . <i>Physica Status Solidi - Rapid Research Letters</i> , 2021, 15, 2100263.	1.2	4
9	The Effect of Interface Diffusion on Raman Spectra of Wurtzite Short-Period GaN/AlN Superlattices. <i>Nanomaterials</i> , 2021, 11, 2396.	1.9	5
10	Quasi-freestanding graphene on SiC(0001) via cobalt intercalation of zero-layer graphene. <i>Physical Review B</i> , 2021, 104, .	1.1	8
11	Mechanical scanning probe lithography of nanophotonic devices based on multilayer TMDCs. <i>Journal of Physics: Conference Series</i> , 2021, 2015, 012020.	0.3	2
12	Dependence of the Characteristics of Spectrally Narrow Luminescence Lines in Nanodiamonds on the Excitation and Temperature Parameters. <i>Physics of the Solid State</i> , 2021, 63, 1170-1175.	0.2	0
13	Investigation of epitaxial graphene via Raman spectroscopy: Origins of phonon mode asymmetries and line width deviations. <i>Carbon</i> , 2020, 170, 666-676.	5.4	12
14	Formation of Iron Silicides Under Graphene Grown on the Silicon Carbide Surface. <i>Physics of the Solid State</i> , 2020, 62, 1944-1948.	0.2	1
15	Structural and Dynamical Properties of Short-Period GaN/AlN Superlattices: Experiment and Theory. <i>Semiconductors</i> , 2020, 54, 1706-1709.	0.2	0
16	A Study of the Photoresponse in Graphene Produced by Chemical Vapor Deposition. <i>Semiconductors</i> , 2020, 54, 991-998.	0.2	0
17	Molecular Beam Epitaxy of Layered Group III Metal Chalcogenides on GaAs(001) Substrates. <i>Materials</i> , 2020, 13, 3447.	1.3	16
18	Detection of lysine molecular ions in solution gated field effect transistors based on unmodified graphene. <i>Journal of Applied Physics</i> , 2020, 128, 215302.	1.1	2

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19	Local anodic oxidation as a method of fabrication optoelectronic devices based on thin TMDC layers. AIP Conference Proceedings, 2020, , .	0.3	1
20	State-of-the-art and prospects for intense red radiation from core-shell InGaN/GaN nanorods. Scientific Reports, 2020, 10, 19048.	1.6	10
21	Intercalation Synthesis of Cobalt Silicides under Graphene Grown on Silicon Carbide. Physics of the Solid State, 2020, 62, 519-528.	0.2	5
22	Photodegradation of surface passivated GaAs nanowires. Journal of Physics: Conference Series, 2020, 1461, 012002.	0.3	1
23	Structural and dynamic properties of short-period GaN/AlN superlattices grown by submonolayer digital epitaxy. Journal of Physics: Conference Series, 2020, 1697, 012155.	0.3	1
24	Raman Studies of Graphene Films Grown on 4H-SiC Subjected to Deposition of Ni. Semiconductors, 2020, 54, 1674-1677.	0.2	0
25	Raman spectra of folded acoustic phonons in short-period GaN/AlN superlattices as a tool for structure characterization. Journal of Physics: Conference Series, 2020, 1697, 012158.	0.3	0
26	Molecular-Beam Epitaxy of Two-Dimensional GaSe Layers on GaAs(001) and GaAs(112) Substrates: Structural and Optical Properties. Semiconductors, 2019, 53, 1131-1137.	0.2	8
27	Template Synthesis of Monodisperse Submicrometer Spherical Nanoporous Silicon Particles. Semiconductors, 2019, 53, 1048-1053.	0.2	2
28	Cobalt Intercalation of Graphene on Silicon Carbide. Physics of the Solid State, 2019, 61, 1316-1326.	0.2	10
29	InSe as a case between 3D and 2D layered crystals for excitons. Nature Communications, 2019, 10, 3479.	5.8	37
30	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. Semiconductors, 2019, 53, 1357-1362.	0.2	2
31	Lattice and magnetic dynamics in the polar, chiral, and incommensurate antiferromagnet Ni_2InSbO_6 . Physical Review B, 2019, 100, .	1.1	8
32	Crystal Structure, Raman Spectroscopy and Dielectric Properties of New Semiorganic Crystals Based on 2-Methylbenzimidazole. Crystals, 2019, 9, 573.	1.0	11
33	MoSe ₂ /graphene/6H-SiC heterojunctions: energy band diagram and photodegradation. Semiconductor Science and Technology, 2019, 34, 125007.	1.0	10
34	Localization and transient emission properties in InGaN/GaN quantum wells of different polarities within core-shell nanorods. Nanoscale, 2019, 11, 193-199.	2.8	10
35	Radiation Defects in Heterostructures 3C-SiC/4H-SiC. Crystals, 2019, 9, 115.	1.0	10
36	Excitonic Emission in van der Waals Nanotubes of Transition Metal Dichalcogenides. Annalen Der Physik, 2019, 531, 1800415.	0.9	28

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73	Site-controlled GaN nanocolumns with InGaN insertions grown by MBE. Journal of Physics: Conference Series, 2017, 917, 032032.	0.3	3
74	Rehybridization of carbon on facets of detonation diamond nanocrystals and forming hydrosols of individual particles. Carbon, 2017, 122, 737-745.	5.4	72
75	New luminescence lines in nanodiamonds obtained by chemical vapor deposition. Physics of the Solid State, 2017, 59, 2407-2412.	0.2	1
76	Transport properties of graphene films grown by thermodestruction of SiC (0001) surface in argon medium. Technical Physics Letters, 2017, 43, 849-852.	0.2	3
77	Lattice dynamics and electronic transitions in a structurally complex layered copper borate <math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Cu</mml:mi><mml:mn>3</mml:mn></mml:msub></math> Physical Review B, 2017, 96, .	1.1	6
78	Study of the crystal and electronic structure of graphene films grown on 6H-SiC (0001). Semiconductors, 2017, 51, 1072-1080.	0.2	44
79	Mode adjustment in hexagonal microresonators with an active region. Journal of Physics: Conference Series, 2016, 741, 012126.	0.3	2
80	Resonance energy transfer in a dense array of II-VI quantum dots. Physics of the Solid State, 2016, 58, 2256-2260.	0.2	2
81	Lattice dynamics and electronic structure of cobalt-titanium spinel Co ₂ TiO ₄ . Physics of the Solid State, 2016, 58, 2516-2522.	0.2	10
82	Supersensitive graphene-based gas sensor. Technical Physics, 2016, 61, 453-457.	0.2	17
83	Optical and Structural Properties of Composite Si:Au Layers Formed by Laser Electrodispersion. Semiconductors, 2016, 50, 418-425.	0.2	2
84	Low-strain heteroepitaxial nanodiamonds: fabrication and photoluminescence of silicon-vacancy colour centres. Nanotechnology, 2016, 27, 395606.	1.3	23
85	Elastic strains and delocalized optical phonons in AlN/GaN superlattices. Semiconductors, 2016, 50, 1043-1048.	0.2	4
86	Graphene-based biosensors. Technical Physics Letters, 2016, 42, 729-732.	0.2	15
87	III-nitride tunable cup-cavities supporting quasi whispering gallery modes from ultraviolet to infrared. Scientific Reports, 2016, 5, 17970.	1.6	13
88	Lattice dynamics and a magnetic-structural phase transition in the nickel orthoborate <math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>N</mml:mi><mml:msub><mml:mi>i</mml:mi></mml:msub></math> <math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>3</mml:mi></mml:msub></math> <math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mo>(</mml:mo></math>	1.1	14
89	Transport properties of graphene in the region of its interface with water surface. Physics of the Solid State, 2016, 58, 1483-1486.	0.2	2
90	Graphene based sensor for environmental monitoring of NO ₂ . Sensors and Actuators B: Chemical, 2016, 236, 1054-1060.	4.0	94

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91	III-nitride microcrystal cavities with quasi whispering gallery modes grown by molecular beam epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 845-852.	0.7	5
92	On the laser detachment of n-GaN films from substrates, based on the strong absorption of IR light by free charge carriers in n+-GaN substrates. Semiconductors, 2016, 50, 699-704.	0.2	4
93	Influence of Substrate Microstructure on the Transport Properties of CVD-Graphene. ACS Applied Materials & Interfaces, 2016, 8, 240-246.	4.0	23
94	Elastic strains effect on frequencies of delocalized polar phonons in AlN/GaN superlattices. AIP Conference Proceedings, 2016, . .	0.3	0
95	The influence of aluminum content on the surface morphology of heavily doped (Al)GaN mesa-strip structures grown by selective metalorganic vapor phase epitaxy. Technical Physics Letters, 2015, 41, 1006-1009.	0.2	0
96	Photoluminescence Spectra of thin ZnO films grown by ALD technology. Physics of the Solid State, 2015, 57, 1865-1869.	0.2	4
97	Optically Addressable Silicon Vacancy-Related Spin Centers in Rhombic Silicon Carbide with High Breakdown Characteristics and ENDOR Evidence of Their Structure. Physical Review Letters, 2015, 115, 247602.	2.9	55
98	Structure and composition of silicon microarrays subjected to cyclic insertion and extraction of lithium. Technical Physics, 2015, 60, 531-540.	0.2	8
99	Gallium nitride nanowires and microwires with exceptional length grown by metal organic chemical vapor deposition via titanium film. Journal of Applied Physics, 2015, 117, 024301.	1.1	8
100	Temperature switching of cavity modes in InN microcrystals. Semiconductors, 2015, 49, 1435-1439.	0.2	0
101	Synthesis of GaN nano- and microwire crystals induced by a titanium nanolayer. Technical Physics Letters, 2014, 40, 372-374.	0.2	5
102	GaN nanowires growth with record growth rate using Ti thin film. Journal of Physics: Conference Series, 2014, 572, 012030.	0.3	0
103	Lattice dynamics of piezoelectric copper metaborate CuB_2O_7 . Physical Review B, 2013, 88, . . .	1.1	20
104	EXAFS study of GaN/AlN multiple quantum wells grown by ammonia MBE. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 311-314.	0.8	8
105	Electron-beam modification of the parameters of the insulator-metal phase transition in vanadium dioxide films. Technical Physics Letters, 2013, 39, 705-708.	0.2	4
106	X-ray diffraction study of short-period AlN/GaN superlattices. Crystallography Reports, 2013, 58, 953-958.	0.1	5
107	Defects and stresses in MBE-grown GaN and Al _{0.3} Ga _{0.7} N layers doped by silicon using silane. Crystallography Reports, 2013, 58, 1023-1029.	0.1	4
108	Characterization of MBE-grown AlGaIn layers heavily doped using silane. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 315-318.	0.8	20

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109	Lattice dynamics of short-period AlN/GaN superlattices: Theory and experiment. Physica Status Solidi (A) Applications and Materials Science, 2013, 210, 484-487.	0.8	12
110	Various types of GaN/InGaN nanostructures grown by MOCVD on Si(111) substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 441-444.	0.8	3
111	MOVPE-grown n-In _x Ga _{1-x} N (x~0.5)/p-Si(111) template as a novel substrate. Proceedings of SPIE, 2013, , .	0.8	2
112	Specific features of Raman spectra of III-V nanowhiskers. Physics of the Solid State, 2011, 53, 1431-1439.	0.2	5
113	Resonant raman scattering and dispersion of polar optical and acoustic phonons in hexagonal inn. Semiconductors, 2010, 44, 161-170.	0.2	4
114	Selective excitation of E_{1L}		

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127	Photoluminescence of n-InN with low electron concentrations. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 50-58.	0.8	5
128	Resonant Raman scattering in InGaN alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 1494-1498.	0.7	3
129	Near-infrared photoluminescence of vertically aligned InN nanorods grown on Si(111) by plasma-assisted molecular-beam epitaxy. <i>Thin Solid Films</i> , 2006, 515, 961-966.	0.8	21
130	Neutron transmutation doping of silicon ³⁰ Si monoisotope with phosphorus. <i>Technical Physics Letters</i> , 2006, 32, 550-553.	0.2	6
131	Near-infrared photoluminescence from vertical InN nanorod arrays grown on silicon: Effects of surface electron accumulation layer. <i>Applied Physics Letters</i> , 2006, 88, 253104.	1.5	80
132	Vibrational Spectra of AlN/GaN Superlattices: Theory and Experiment. <i>Physics of the Solid State</i> , 2005, 47, 742.	0.2	11
133	GaN Films Grown by Vapor-Phase Epitaxy in a Hydride-Chloride System on Si(111) Substrates with AlN Buffer Sublayers. <i>Technical Physics Letters</i> , 2005, 31, 915.	0.2	8
134	Optical phonons in hexagonal GaN/AlN and GaN/AlGaN superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 2389-2393.	0.8	4
135	Manifestation of the equilibrium hole distribution in photoluminescence of n-InN. <i>Physica Status Solidi (B): Basic Research</i> , 2005, 242, R33-R35.	0.7	7
136	A gauge invariant approach to the Raman scattering in heavily doped crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2005, 242, R58-R60.	0.7	1
137	Urbach tails of valence and conductivity bands and optical spectra of hexagonal InN near the fundamental band gap. <i>AIP Conference Proceedings</i> , 2005, , .	0.3	0
138	Acceptor states in the photoluminescence spectra of n-InN. <i>Physical Review B</i> , 2005, 71, .	1.1	135
139	Fullerene films highly resistant to laser radiation. <i>Technical Physics</i> , 2004, 49, 258-262.	0.2	2
140	Deformation of AlGaIn/GaN superlattice layers according to x-ray diffraction data. <i>Physics of the Solid State</i> , 2004, 46, 364-370.	0.2	8
141	Electronic and vibrational states in InN and In _x Ga _{1-x} N solid solutions. <i>Semiconductors</i> , 2004, 38, 861-898.	0.2	66
142	IR reflection of optical phonons in GaN/AlGaIn superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 2733-2736.	0.8	1
143	Correlations between electrical and optical properties for OMVPE InN. <i>Journal of Crystal Growth</i> , 2004, 261, 275-279.	0.7	36
144	Iron disilicide formed in a-Si _{1-x} Fe _x thin films by magnetron co-sputtering. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 939-943.	1.3	3

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145	Stress-induced changes of thermal donor formation in heat-treated Czochralski-grown silicon. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 769-772.	1.3	8
146	Energy gap and optical properties of $\text{In}_x\text{Ga}_{1-x}\text{N}$. <i>Physica Status Solidi A</i> , 2003, 195, 628-633.	1.7	92
147	Bulk gallium nitride: preparation and study of properties. <i>Physica Status Solidi A</i> , 2003, 195, 122-126.	1.7	4
148	Photoluminescence and Raman study of hexagonal InN and In-rich InGaN alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 240, 425-428.	0.7	27
149	Lattice dynamics and Raman spectra of strained hexagonal GaN/AlN and GaN/AlGaN superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 2035-2038.	0.8	11
150	Shallow donor centers in gallium nitrides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003, 0, 601-604.	0.8	5
151	Bulk large-area GaN layers. <i>Technical Physics Letters</i> , 2003, 29, 400-403.	0.2	1
152	Resonant Raman scattering spectra in a ZnCdSe/ZnSe structure with a quantum well and open nanowires. <i>Physics of the Solid State</i> , 2003, 45, 1374-1378.	0.2	2
153	Single-crystalline InN films with an absorption edge between 0.7 and 2 eV grown using different techniques and evidence of the actual band gap energy. <i>Applied Physics Letters</i> , 2003, 83, 4788-4790.	1.5	91
154	<title>Bandgap of hexagonal InN and InGaN alloys</title>. , 2002, , .		2
155	<title>Raman studies as a tool for characterization of the strained hexagonal GaN/Al$\langle \text{inf} \rangle \langle \text{roman} \rangle x \langle \text{roman} \rangle \langle \text{inf} \rangle \langle \text{roman} \rangle Ga \langle \text{roman} \rangle 1-x \langle \text{roman} \rangle \langle \text{inf} \rangle \langle \text{roman} \rangle N$ superlattices</title>. , 2002, , .		0
156	Composition dependence of optical phonon energies and Raman line broadening in hexagonal $\text{Al}_x\text{Ga}_{1-x}\text{N}$ alloys. <i>Physical Review B</i> , 2002, 65, .	1.1	145
157	Investigation of vacancy-type complexes in GaN and AlN using positron annihilation. <i>Semiconductors</i> , 2002, 36, 1106-1110.	0.2	3
158	The formation of FeSi_2 precipitates in microcrystalline Si. <i>Semiconductors</i> , 2002, 36, 1235-1239.	0.2	2
159	Isotope-pure ^{28}Si layers grown by VPE. <i>Semiconductors</i> , 2002, 36, 1398-1399.	0.2	1
160	Isotope-pure silicon layers grown by MBE. <i>Semiconductors</i> , 2002, 36, 1400-1402.	0.2	2
161	Phase transition-governed opal-like VO_2 photonic crystal. <i>Applied Physics Letters</i> , 2001, 79, 2127-2129.	1.5	84
162	Study of the correlation between GaN material properties and the growth conditions of radio frequency plasma-assisted molecular beam epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001, 80, 304-308.	1.7	8

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163	Anisotropic Superconductivity of InN Grown by Molecular Beam Epitaxy on Sapphire (0001). <i>Physica Status Solidi (B): Basic Research</i> , 2001, 228, 9-12.	0.7	13
164	Preparation and properties of isotopically pure polycrystalline silicon. <i>Semiconductors</i> , 2001, 35, 877-879.	0.2	4
165	Fabrication and structure of an opal-gallium nitride nanocomposite. <i>Semiconductor Science and Technology</i> , 2001, 16, L5-L7.	1.0	17
166	Electronic and structural properties of InN thin films grown by MOMBE on sapphire substrates. , 2000, , .		2
167	Fabrication and structural studies of opal-III nitride nanocomposites. <i>Nanotechnology</i> , 2000, 11, 291-294.	1.3	27
168	Statistical Ga clusters and Al(TO) gap mode in Al _x Ga _{1-x} N alloys. <i>Physical Review B</i> , 2000, 62, 2522-2535.	1.1	8
169	Point defects in gamma-irradiated n-GaN. <i>Semiconductor Science and Technology</i> , 2000, 15, 73-78.	1.0	40
170	Strain relaxation in GaN layers grown on porous GaN sublayers. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999, 4, 1.	1.0	48
171	Specific structural features and thermal resistance of shungite carbon to graphitization. <i>Physics of the Solid State</i> , 1999, 41, 1291-1294.	0.2	14
172	Influence of rapid high-temperature anneals on the photoluminescence of erbium-doped GaN in the wavelength interval 1.0–1.6 Åµm. <i>Semiconductors</i> , 1999, 33, 1-5.	0.2	4
173	MBE Growth of Hexagonal InN Films on Sapphire with Different Initial Growth Stages. <i>Physica Status Solidi A</i> , 1999, 176, 247-252.	1.7	41
174	Mg-Doped Hexagonal InN/Al ₂ O ₃ Films Grown by MBE. <i>Physica Status Solidi A</i> , 1999, 176, 373-378.	1.7	29
175	Experimental and theoretical studies of phonons in hexagonal InN. <i>Applied Physics Letters</i> , 1999, 75, 3297-3299.	1.5	251
176	Phonon dispersion and Raman scattering in hexagonal GaN and AlN. <i>Physical Review B</i> , 1998, 58, 12899-12907.	1.1	741
177	Anomalies in the microwave conductivity of a polycrystalline C ₆₀ membrane. <i>Physics of the Solid State</i> , 1998, 40, 532-534.	0.2	1
178	Crystalline structure of a C ₆₀ /C ₇₀ membrane. <i>Physics of the Solid State</i> , 1998, 40, 535-538.	0.2	2
179	Physical Properties of Bulk GaN Crystals Grown by HVPE. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1997, 2, 1.	1.0	53
180	Raman and photoluminescence studies of biaxial strain in GaN epitaxial layers grown on 6H-SiC. <i>Journal of Applied Physics</i> , 1997, 82, 5097-5102.	1.1	354

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181	Diamond-graphite phase transition in ultradisperse-diamond clusters. <i>Physics of the Solid State</i> , 1997, 39, 1007-1015.	0.2	131
182	Raman scattering spectra and electrical conductivity of thin silicon films with a mixed amorphous-nanocrystalline phase composition: Determination of the nanocrystalline volume fraction. <i>Physics of the Solid State</i> , 1997, 39, 1197-1201.	0.2	33
183	Nanoscale-crystallite nucleation and growth in amorphous solids. <i>Physical Review B</i> , 1995, 52, 955-966.	1.1	26
184	Formation and Raman spectroscopic study of YBCO/STO/YBCO heteroepitaxial structures. <i>Superconductor Science and Technology</i> , 1994, 7, 727-733.	1.8	8
185	Bolometric properties of YBaCuO films on mica substrates. <i>Physica C: Superconductivity and Its Applications</i> , 1994, 235-240, 3393-3394.	0.6	0
186	The formation of two-layered YBa ₂ Cu ₃ O _{7-δ} superconducting films and their microwave surface resistance. <i>Superconductor Science and Technology</i> , 1993, 6, 23-29.	1.8	20
187	The influence of growth temperature on the structural characteristics of YBa ₂ Cu ₃ O _{7-δ} films: a Raman scattering study. <i>Superconductor Science and Technology</i> , 1993, 6, 819-821.	1.8	9
188	Comparative low-frequency noise studies of YBaCuO films. <i>AIP Conference Proceedings</i> , 1993, , .	0.3	3
189	Characteristics of epitaxial Y-Ba-Cu-O thin films grown by aerosol MOCVD technique. <i>Superconductor Science and Technology</i> , 1990, 3, 493-496.	1.8	24
190	Lattice dynamics of ferroelectric NaNO ₂ by two-phonon Raman scattering and infrared absorption. <i>Ferroelectrics</i> , 1978, 21, 337-338.	0.3	4
191	The "destructive" fermi resonance. <i>Physica Status Solidi (B): Basic Research</i> , 1977, 79, 347-357.	0.7	1
192	On fermi resonance theory. <i>Physica Status Solidi (B): Basic Research</i> , 1976, 78, 359-370.	0.7	4